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With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China







Thyristor \ Diode Module

= 2x 1600 V

140 A

 V_{T} 1.28 V

Phase leg

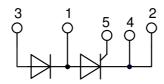
Part number

MCMA140PD1600TB



Backside: isolated

F1 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 4800 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- · Reduced weight
- Advanced power cycling

Terms _Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

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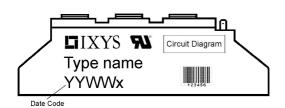


Rectifier				Ì	Ratings		1
Symbol	Definition	Conditions		min.	typ.	max.	Un
V _{RSM/DSM}	max. non-repetitive reverse/forwa	rd blocking voltage	$T_{VJ} = 25^{\circ}C$			1700	'
V _{RRM/DRM}	max. repetitive reverse/forward bl	<u> </u>	$T_{VJ} = 25^{\circ}C$			1600	'
I _{R/D}	reverse current, drain current	$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 25^{\circ}C$			100	μ
		$V_{R/D} = 1600 \text{ V}$	$T_{VJ} = 140$ °C			10	m
V _T	forward voltage drop	$I_T = 150 A$	$T_{VJ} = 25^{\circ}C$			1.29	,
		$I_T = 300 A$				1.63	١
		$I_{T} = 150 \text{ A}$	T _{VJ} = 125°C			1.28	,
		$I_T = 300 \text{ A}$				1.70	,
I _{TAV}	average forward current	T _C = 85°C	T _{vJ} = 140°C			140	1
I _{T(RMS)}	RMS forward current	180° sine				220	,
V _{T0}	threshold voltage		T _{vJ} = 140°C			0.85	١
r _T	slope resistance	oss calculation only				2.8	m۵
R _{thJC}	thermal resistance junction to cas	e				0.22	K/V
R _{thCH}	thermal resistance case to heatsii				0.20		K/V
P _{tot}	total power dissipation		T _C = 25°C		0.20	520	٧
I _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{v,l} = 45^{\circ}C$			2.40	k/
*15M		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			2.59	k/
		t = 0.0 ms; (50 Hz), sine	T _{v.i} = 140°C			2.04	k,
		t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			2.21	k
l²t	value for fusing	t = 0.5 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			28.8	kA ²
	value for fushing	t = 8.3 ms; (60 Hz), sine	$V_R = 0 V$			27.9	kA ²
		t = 0.5 ms; (50 Hz), sine t = 10 ms; (50 Hz), sine	$V_{R} = 0 V$ $T_{V,I} = 140 ^{\circ}C$			20.8	kA ²
		* * * * * * * * * * * * * * * * * * * *	• •				į
^	iunation canacitanas	t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$		110	20.2	!
C,	junction capacitance	V _R = 400 V f = 1 MHz	$T_{VJ} = 25^{\circ}C$		119	40	pl
P_{GM}	max. gate power dissipation	$t_P = 30 \mu s$	$T_{C} = 140^{\circ}C$			10	۷
_		$t_{P} = 300 \mu s$				5	۷
P _{GAV}	average gate power dissipation					0.5	V
(di/dt) _{cr}	critical rate of rise of current		epetitive, $I_T = 450 A$			150	A/μ
		$t_P = 200 \mu s; di_G/dt = 0.45 A/\mu s;$					
			on-repet., $I_T = 150 A$			500	A/μ
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140$ °C			1000	V/µ
		R _{GK} = ∞; method 1 (linear volta					
V_{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$			1.5	١
			$T_{VJ} = -40$ °C			1.6	١
I _{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$			150	m/
			$T_{VJ} = -40$ °C			200	m
V _{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DRM}$	$T_{VJ} = 140^{\circ}C$			0.2	١
I _{GD}	gate non-trigger current					10	m
I _L	latching current	t _p = 10 μs	T _{VJ} = 25°C			200	m
		$I_G = 0.45 \text{A}; di_G/dt = 0.45 \text{A/}\mu s$	3				İ
I _H	holding current	V _D = 6 V R _{GK} = ∞	$T_{VJ} = 25^{\circ}C$			200	m
t _{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$	$T_{VJ} = 25$ °C			2	μ
gu	- ,	$I_{\rm G} = 0.45 \text{A}; \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu \text{s}$				_	٣
+	turn-off time	$V_{\rm R} = 100 \text{ V}; \ I_{\rm T} = 150 \text{ A}; \ V = \frac{2}{3}$			185		- 11
tq		$V_R = 100 \text{ V}, I_T = 130 \text{ A}, V = 7$ $di/dt = 10 \text{ A}/\mu \text{s} \text{ dv/dt} = 20 \text{ V}$			100		μ



MCMA140PD1600TB

Package TO-240AA			Ratings					
Symbol	Definition	Conditions			min.	typ.	max.	Unit
I _{RMS}	RMS current	per terminal					200	Α
T _{VJ}	virtual junction temperature				-40		140	°C
Top	operation temperature			-40		125	°C	
T _{stg}	storage temperature			-40		125	°C	
Weight						81		g
M _D	mounting torque				2.5		4	Nm
$\mathbf{M}_{_{\mathbf{T}}}$	terminal torque				2.5		4	Nm
d _{Spp/App}	araanaga diatanaa an aurfa	ce striking distance through air	terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}	creepage distance on surface	ce striking distance through an	terminal to backside	16.0	16.0			mm
V _{ISOL}	isolation voltage	t = 1 second			4800			٧
1002		t = 1 minute	50/60 Hz, RMS; IsoL ≤ 1 mA		4000			٧



Part description

M = Module

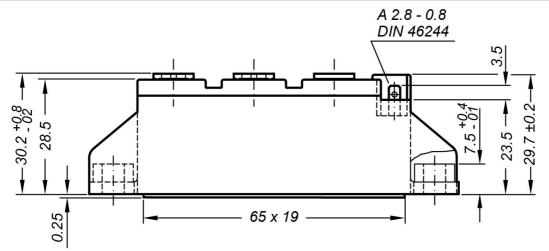
M = Module
C = Thyristor (SCR)
M = Thyristor
A = (up to 1800V)
140 = Current Rating [A]
PD = Phase leg
1600 = Reverse Voltage [V]
TB = TO-240AA-1B

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCMA140PD1600TB	MCMA140PD1600TB	Box	36	509348

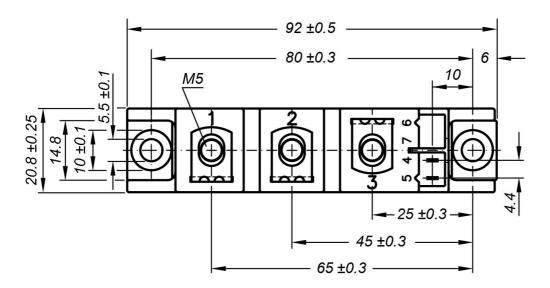
Equiva	alent Circuits for	Simulation	* on die level	$T_{VJ} = 140 ^{\circ}\text{C}$
$I \rightarrow V_0$	R_0	Thyristor		
V _{0 max}	threshold voltage	0.85		V
$R_{0 \text{ max}}$	slope resistance *	1.6		$m\Omega$



Outlines TO-240AA

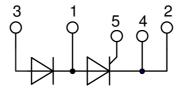


General tolerance: DIN ISO 2768 class "c"



Optional accessories: Keyed gate/cathode twin plugs Wire length: 350 mm, gate = white, cathode = red UL 758, style 3751

Type **ZY 200L** (L = Left for pin pair 4/5)





Thyristor

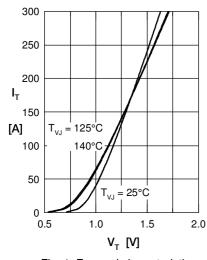


Fig. 1 Forward characteristics

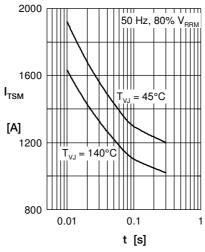


Fig. 2 Surge overload current I_{TSM} : crest value, t: duration

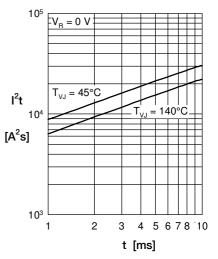


Fig. 3 I²t versus time (1-10 s)

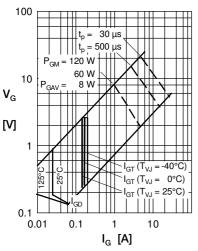


Fig. 4 Gate voltage & gate current

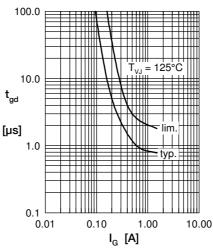


Fig. 5 Gate controlled delay time t_{ad}

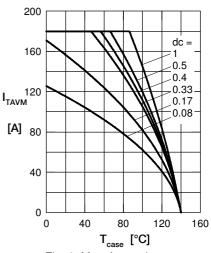


Fig. 6 Max. forward current at case temperature

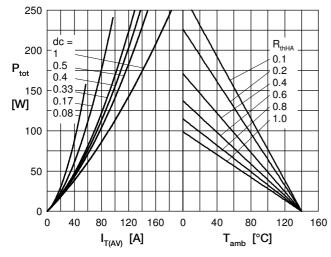


Fig. 7a Power dissipation versus direct output current

Fig. 7b and ambient temperature

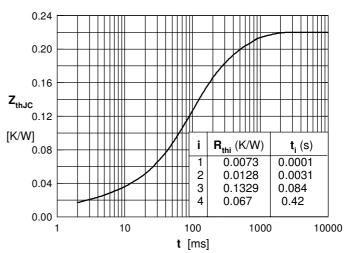


Fig. 8 Transient thermal impedance junction to case